TLP521GB, TLP521-2GB, TLP521-4GB, TLP521, TLP521-2, TLP521-4
TLP521XGB, TLP521-2XGB, TLP521-4XGB
TLP521X, TLP521-2X, TLP521-4X

HIGH DENSITY MOUNTING PHOTOTRANSISTOR OPTICALLY COUPLED ISOLATORS

APPROVALS

- UL recognised, File No. E91231

'X' SPECIFICATION APPROVALS

- VDE 0884 in 3 available lead form : -
  - STD
  - G form
  - SMD approved to CECC 00802
- BSI approved - Certificate No. 8001

DESCRIPTION

The TLP521, TLP521-2, TLP521-4 series of optically coupled isolators consist of infrared light emitting diodes and NPN silicon photo transistors in space efficient dual in line plastic packages.

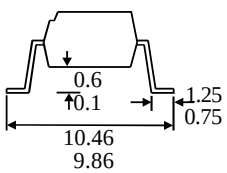
FEATURES

- Options :-
  10mm lead spread - add G after part no.
  Surface mount - add SM after part no.
  Tape&reel - add SMT&R after part no.
- High Current Transfer Ratio (50% min)
- High Isolation Voltage ($5.3kV_{RMS}$,$7.5kV_{PK}$)
- High BV_{CEO} (55Vmin)
- All electrical parameters 100% tested
- Custom electrical selections available

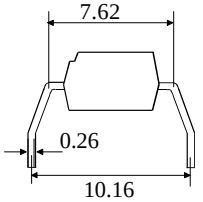
APPLICATIONS

- Computer terminals
- Industrial systems controllers
- Measuring instruments
- Signal transmission between systems of different potentials and impedances

OPTION SM
SURFACE MOUNT

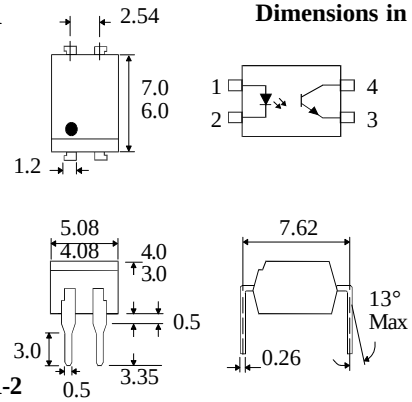


OPTION G

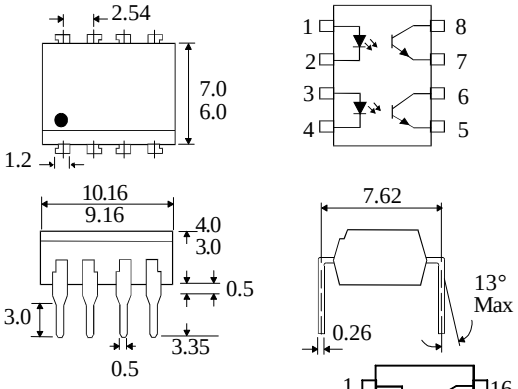


TLP521

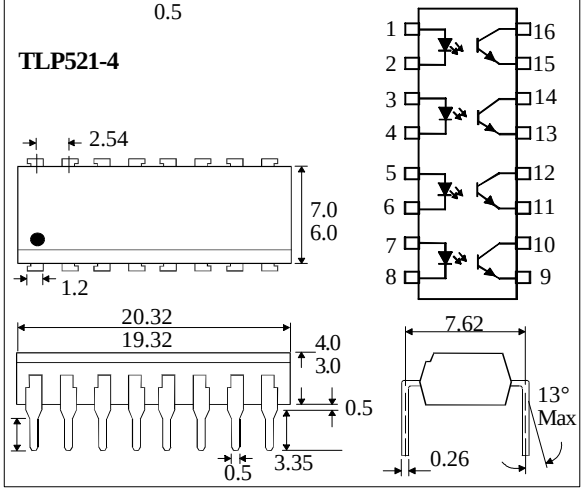
Dimensions in mm



TLP521-2



TLP521-4



ISOCOM COMPONENTS LTD
Unit 25B, Park View Road West,
Park View Industrial Estate, Brenda Road
Hartlepool, Cleveland, TS25 1YD
Tel: (01429) 863609 Fax :(01429) 863581

ABSOLUTE MAXIMUM RATINGS
(25°C unless otherwise specified)

Storage Temperature	-55°C to + 125°C
Operating Temperature	-30°C to + 100°C
Lead Soldering Temperature (1/16 inch (1.6mm) from case for 10 secs)	260°C

INPUT DIODE

Forward Current	50mA
Reverse Voltage	6V
Power Dissipation	70mW

OUTPUT TRANSISTOR

Collector-emitter Voltage BV_{CEO}	55V
Emitter-collector Voltage BV_{ECO}	6V
Power Dissipation	150mW

POWER DISSIPATION

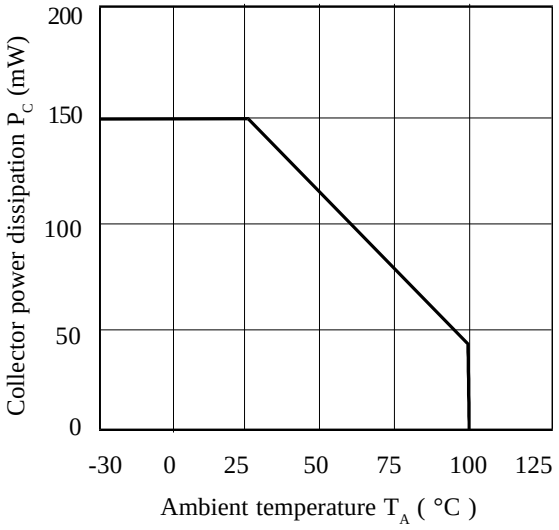
Total Power Dissipation (derate linearly 2.67mW/°C above 25°C)	200mW

ELECTRICAL CHARACTERISTICS (T_A = 25°C Unless otherwise noted)

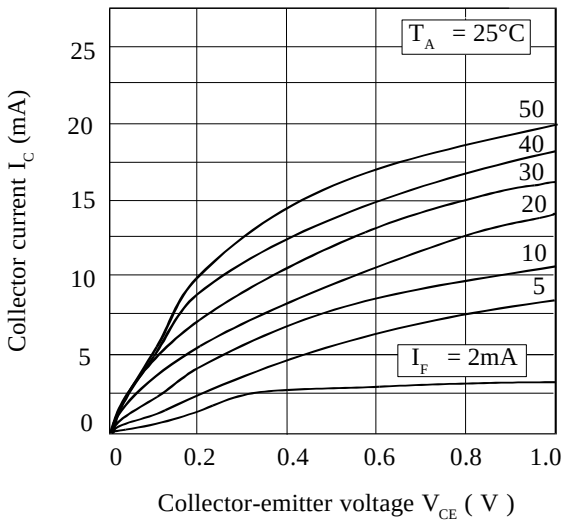
PARAMETER		MIN	TYP	MAX	UNITS	TEST CONDITION
Input	Forward Voltage (V_F)	1.0	1.15	1.3	V	I_F = 10mA
	Reverse Current (I_R)			10	µA	V_R = 4V
Output	Collector-emitter Breakdown (BV_{CEO}) (Note 2)	55			V	I_C = 0.5mA
	Emitter-collector Breakdown (BV_{ECO})	6			V	I_E = 100µA
	Collector-emitter Dark Current (I_{CEO})			100	nA	V_{CE} = 20V
Coupled	Current Transfer Ratio (CTR) (Note 2)					
	TLP521, TLP521-2, TLP521-4	50		600	%	5mA I_F, 5V V_{CE}
	CTR selection available BL	200		600	%	
	GB	100		600	%	
	GB	30			%	1mA I_F, 0.4V V_{CE}
	Collector-emitter Saturation Voltage $V_{CE\ (SAT)}$			0.4	V	8mA I_F, 2.4mA I_C
	-GB			0.4	V	1mA I_F, 0.2mA I_C
	Input to Output Isolation Voltage V_{ISO}	5300			V_{RMS}	See note 1
		7500			V_{PK}	See note 1
	Input-output Isolation Resistance R_{ISO}	$5x10^{10}$			Ω	V_{IO} = 500V (note 1)
	Response Time (Rise), tr		4		µs	V_{CE} = 2V,
	Response Time (Fall), tf		3		µs	I_C = 2mA, R_L = 100Ω

Note 1 Measured with input leads shorted together and output leads shorted together.
Note 2 Special Selections are available on request. Please consult the factory.

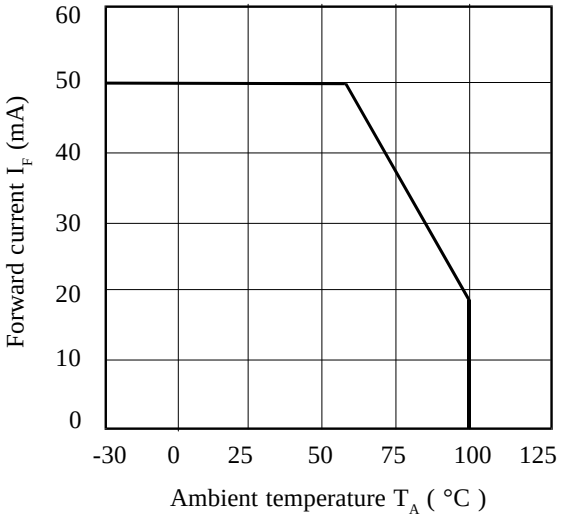
Collector Power Dissipation vs. Ambient Temperature



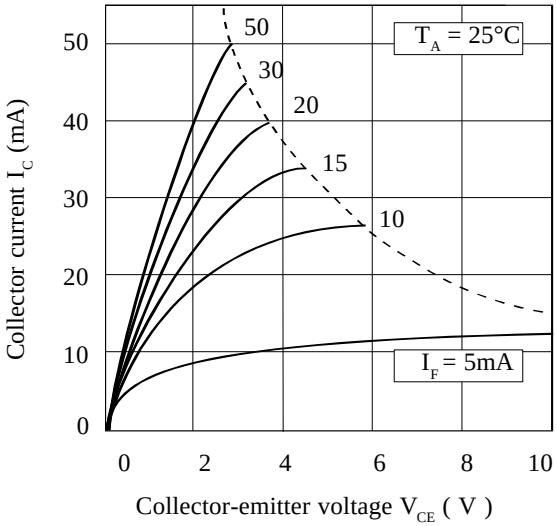
Collector Current vs. Low Collector-emitter Voltage



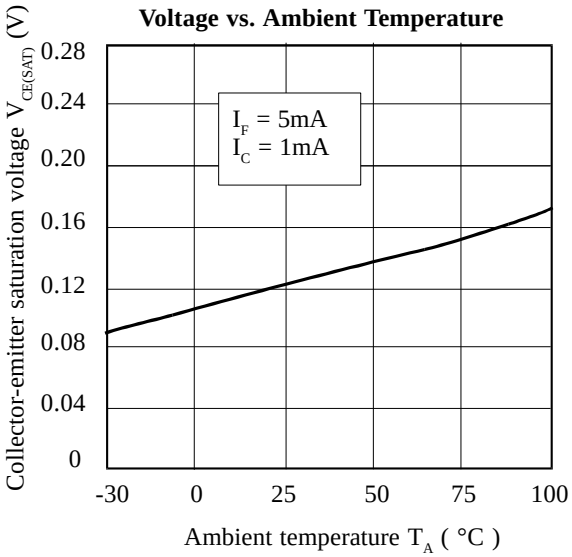
Forward Current vs. Ambient Temperature



Collector Current vs. Collector-emitter Voltage



Collector-emitter Saturation Voltage vs. Ambient Temperature



Current Transfer Ratio vs. Forward Current